



STC5NF30V

N-channel 30V - 0.027Ω - 5A - TSSOP8
2.7V-drive STripFET™ II Power MOSFET

General features

| Type | V _{DSS} | R _{DS(on)} | I _D |
|-----------|------------------|--|----------------|
| STC5NF30V | 30V | < 0.031 Ω (@ 4.5 V) < 0.035 Ω (@ 2.7 V) | 5A |

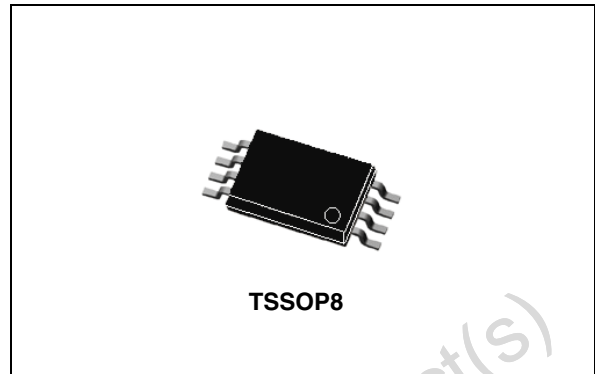
- Ultra low threshold gate drive (2.7V)
- Standard outline for easy automated surface mount assembly

Description

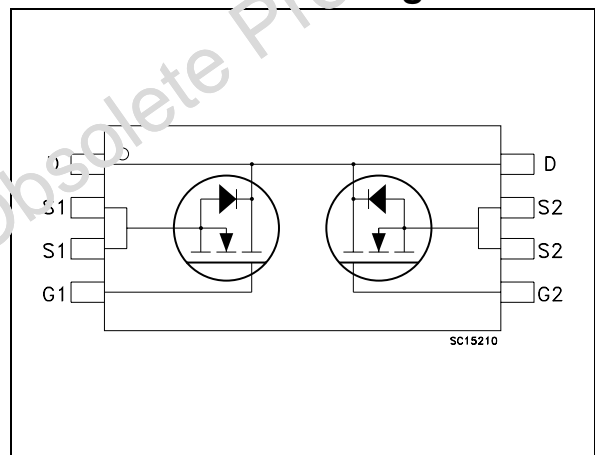
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

- Switching application



Internal schematic diagram



Order codes

| Part number | Marking | Package | Packaging |
|-------------|---------|---------|-----------|
| STC5NF30V | C5NF30V | TSSOP8 | |

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Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|---|------------|------------|
| V_{DS} | Drain-source voltage ($V_{GS} = 0$) | 30 | V |
| V_{DGR} | Drain-gate voltage ($R_{GS} = 20K\Omega$) | 20 | V |
| V_{GS} | Gate-source voltage | ± 12 | V |
| I_D | Drain current (continuous) at $T_C = 25^\circ C$ | 5 | A |
| I_D | Drain current (continuous) at $T_C = 100^\circ C$ | 3 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 20 | A |
| P_{TOT} | Total dissipation at $T_C = 25^\circ C$ | 1.5 | W |
| T_{stg} | Storage temperature | -55 to 150 | $^\circ C$ |
| T_J | Max. operating junction temperature | -55 to 150 | $^\circ C$ |

1. Pulse width limited by safe operating area

Table 2. Thermal data

| Symbol | Parameter | Value | Unit |
|---------------|-------------------------------------|---------------------|--------------|
| $R_{thJ-PBC}$ | Thermal resistance junction-PBC Max | 100 ⁽¹⁾ | $^\circ C/W$ |
| $R_{thJ-PBC}$ | Thermal resistance junction-PBC Max | 83.5 ⁽²⁾ | $^\circ C/W$ |

1. When Mounted on FR-4 board with 1 inch² pad, 2 oz of Cu and t = 10 sec

2. When Mounted on minimum recommended footprint

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 3. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|----------------|----------------|--------------------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 250\mu\text{A}$, $V_{GS} = 0$ | 30 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating @ } 125^{\circ}\text{C}$ | | | 1 10 | μA μA |
| I_{GSS} | Gate body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 12\text{V}$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$ | 0.6 | | | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 4.5\text{V}$, $I_D = 2.5\text{A}$ $V_{GS} = 2.7\text{V}$, $I_D = 2.5\text{A}$ | | 0.027 0.031 | 0.031 0.035 | Ω Ω |

Table 4. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|---|---|------|-------------------|------|----------------|
| $g_{fs}^{(1)}$ | Forward transconductance | $V_{DS} = 15\text{V}$, $I_D = 2.5\text{A}$ | | 9.5 | | S |
| C_{iss} C_{oss} C_{rss} | Input capacitance Output capacitance Reverse transfer capacitance | $V_{DS} = 15\text{V}$, $f = 1\text{MHz}$, $V_{GS} = 0$ | | 460 200 50 | | pF pF pF |
| Q_g Q_{gs} Q_{gd} | Total gate charge Gate-source charge Gate-drain charge | $V_{DD} = 16\text{V}$, $I_D = 4.5\text{A}$ $V_{GS} = 4.5\text{V}$ <i>Figure 15 on page 8</i> | | 8.5 1.8 2.4 | 11.5 | nC nC nC |

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 5. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|------|---------------------|------|----------------------|
| $t_{d(on)}$ t_r $t_{d(off)}$ t_f | Turn-on delay time Rise time Turn-off delay time Fall time | $V_{DD} = 10\text{V}$, $I_D = 2.5\text{A}$, $R_G = 4.7\Omega$, $V_{GS} = 4.5\text{V}$ <i>Figure 13 on page 8</i> | | 7 33 27 10 | | ns ns ns ns |
| $t_{d(off)}$ t_f t_c | Off-voltage rise time Fall time Cross-over time | $V_{clamp} = 16\text{V}$, $I_D = 5\text{A}$ $R_G = 4.7\Omega$, $V_{GS} = 4.5\text{V}$ <i>Figure 15 on page 8</i> | | 26 11 21 | | ns ns ns |

Table 6. Source drain diode

| Symbol | Parameter | Test conditions | Min | Typ. | Max | Unit |
|-----------------------------------|--|---|-----|---------------|-----|--------------------|
| I_{SD} | Source-drain current | | | | 5 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | | | 20 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 5A, V_{GS} = 0$ | | | 1.2 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD} = 5A,$ $di/dt = 100A/\mu s,$ $V_{DD} = 10V, T_J = 150^\circ C$ Figure 15 on page 8 | | 26 13 1 | | ns μC A |

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

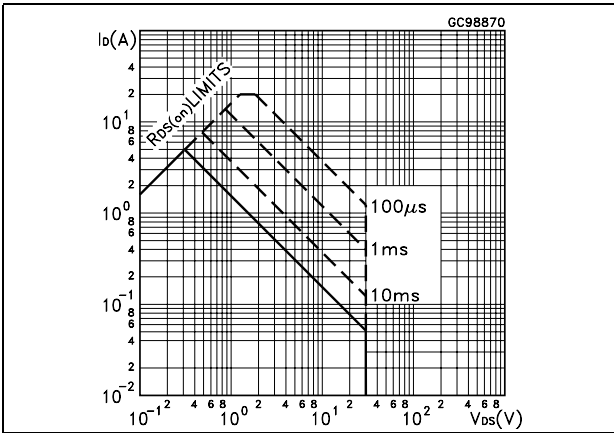


Figure 2. Thermal impedance

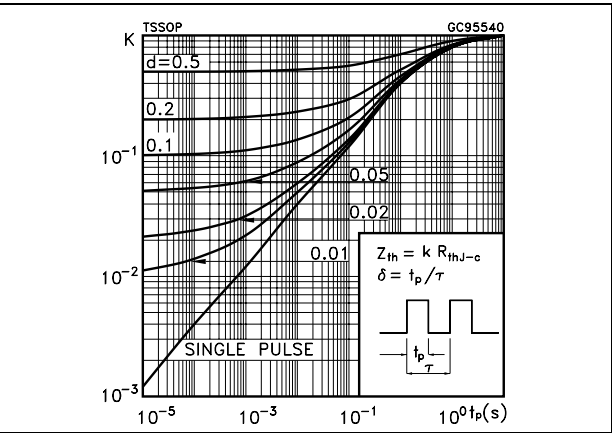


Figure 3. Output characteristics

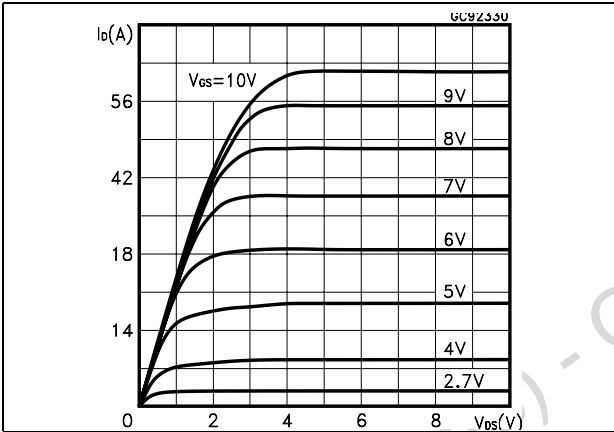


Figure 4. Transfer characteristics

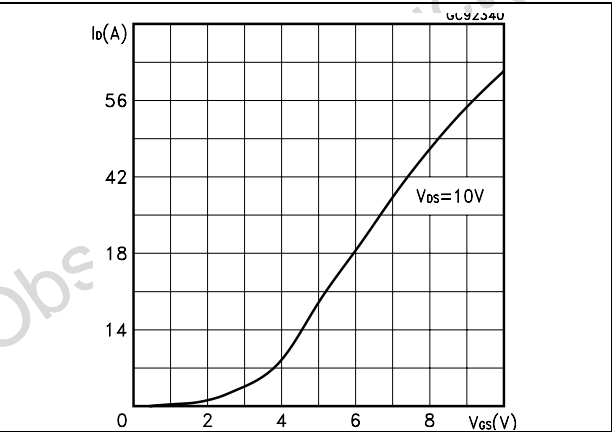


Figure 5. Transconductance

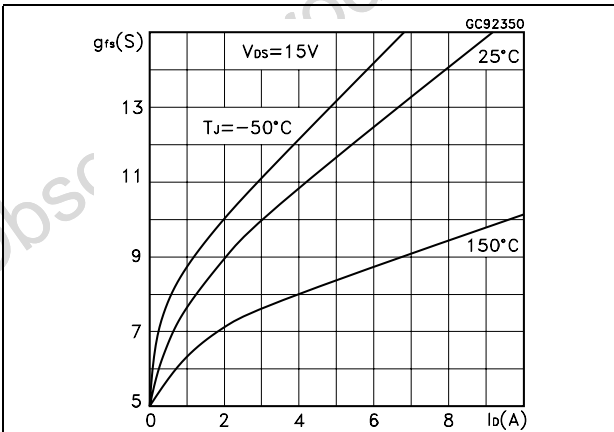


Figure 6. Static drain-source on resistance

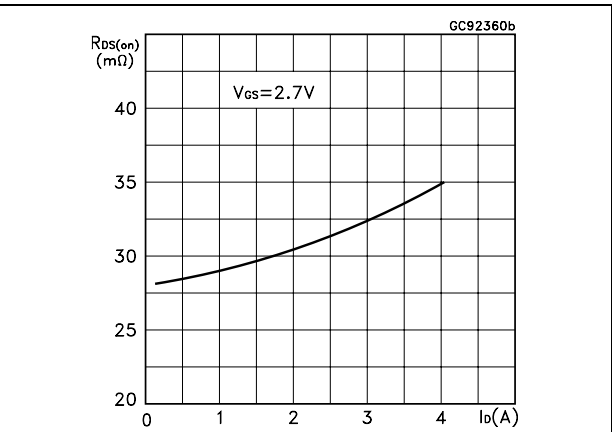


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

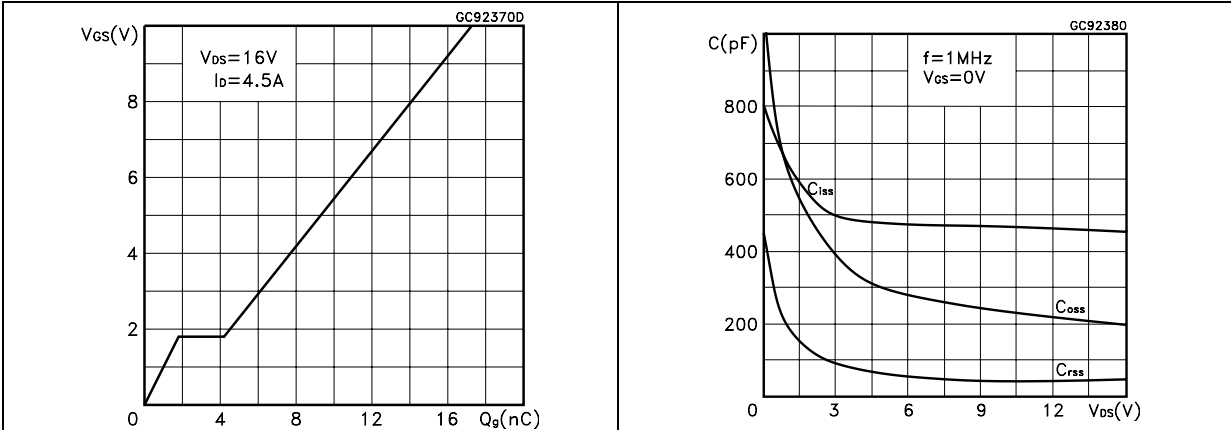


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

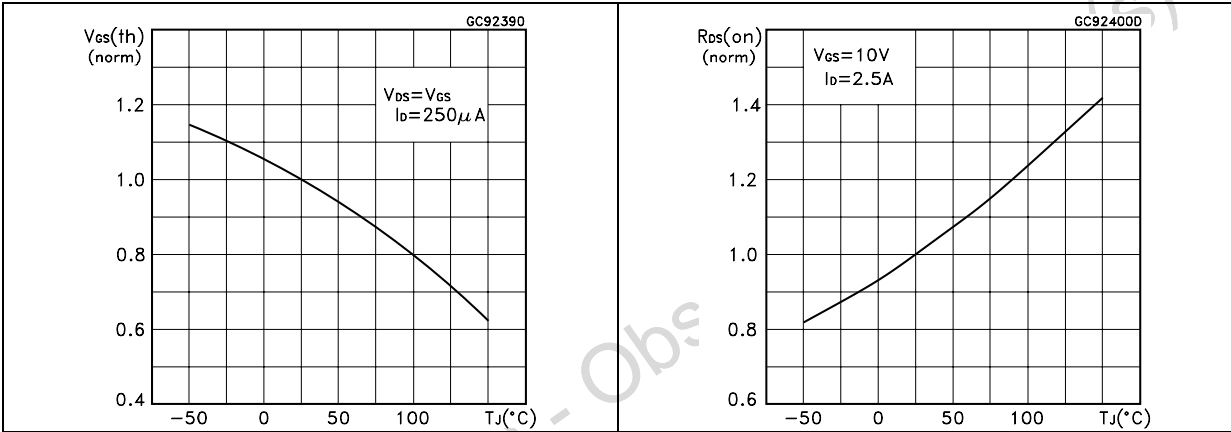
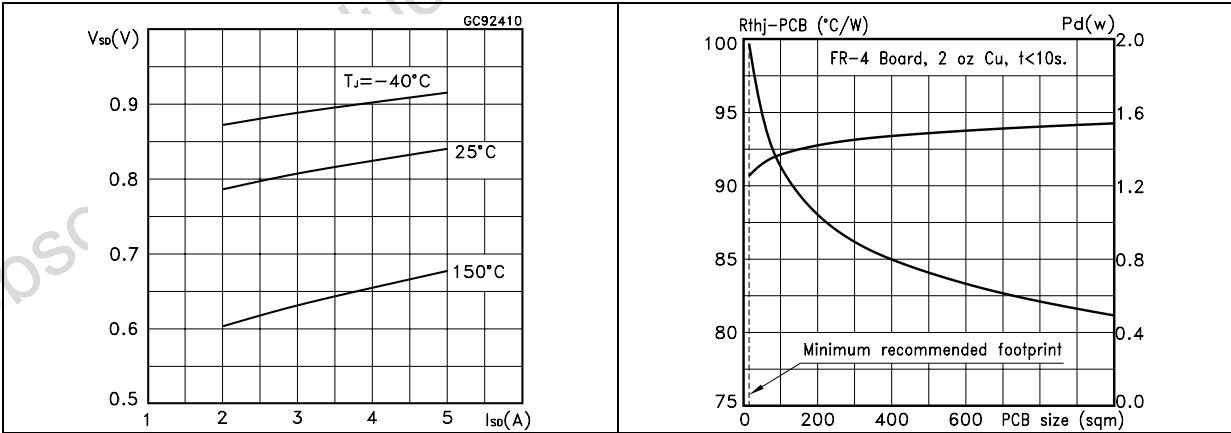


Figure 11. Source-drain diode forward characteristics Figure 12. Thermal resistance and max power



3 Test circuit

Figure 13. Switching times test circuit for resistive load

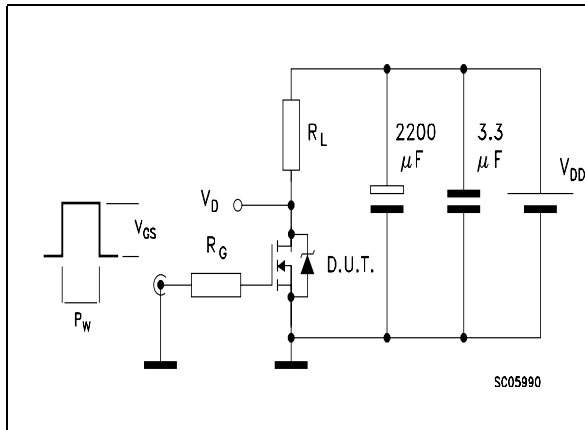


Figure 14. Gate charge test circuit

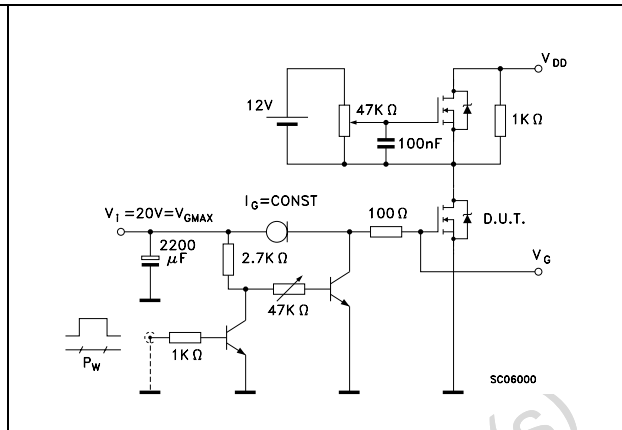


Figure 15. Test circuit for inductive load switching and diode recovery times

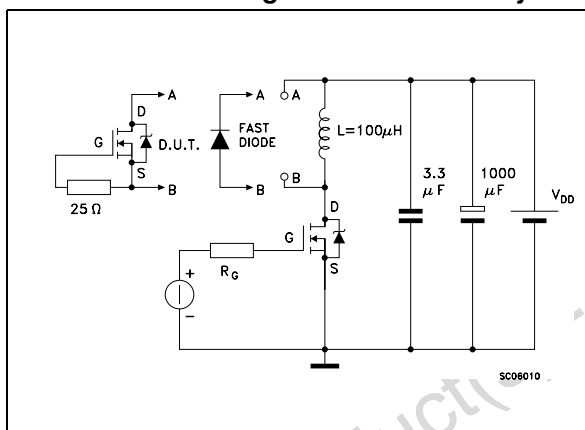


Figure 16. Unclamped Inductive load test circuit

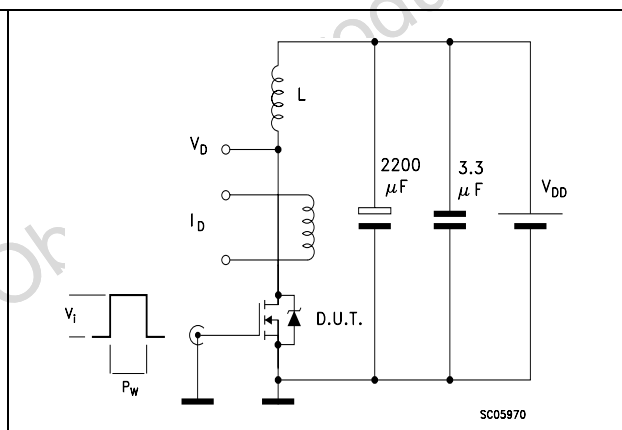
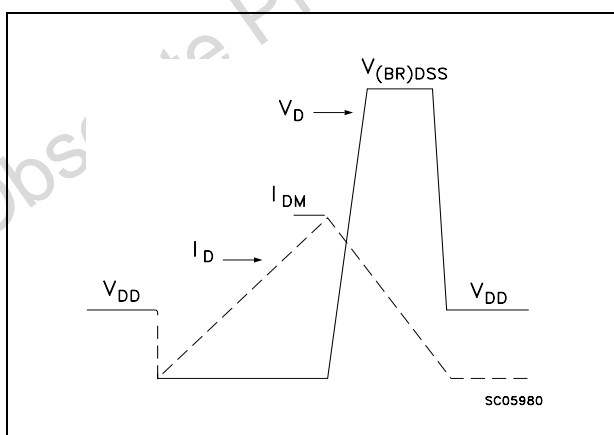


Figure 17. Unclamped inductive waveform



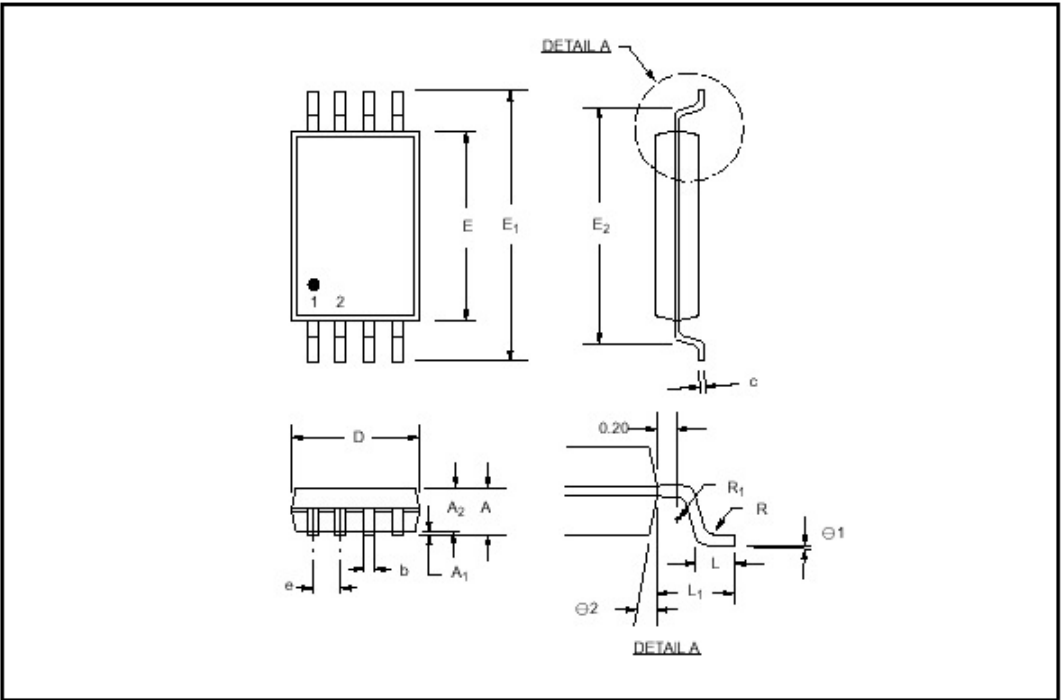
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s) - Obsolete Product(s)

TSSOP8 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|------|-------|------|--------|-------|--------|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | 1.05 | | 1.20 | 0.041 | | 0.047 |
| A1 | 0.05 | | 0.15 | 0.002 | | 0.006 |
| A2 | 0.80 | | 1.05 | 0.032 | | 0.041 |
| b | 0.19 | | 0.30 | 0.008 | | 0.012 |
| c | | 0.127 | | | 0.005 | |
| D | 2.90 | | 3.10 | 0.114 | | 0.122 |
| E | 4.30 | | 4.50 | 0.170 | | 0.177 |
| E1 | 6.20 | | 6.60 | 0.240 | | 0.260 |
| E2 | 5.14 | | 5.24 | 0.202 | | 0.206 |
| e | | 0.65 | | | 0.025 | |
| L | 0.45 | | 0.75 | 0.018 | | 0.030 |
| L1 | 0.90 | | 1.10 | 0.0355 | | 0.0433 |
| R | 0.09 | | | 0.004 | | |
| R1 | 0.09 | | | 0.004 | | |
| θ1 | 0° | | 8° | 0° | | 8° |
| θ2 | 12° | | | | | |



5 Revision history

Table 7. Revision history

| Date | Revision | Changes |
|-------------|----------|---------------------------|
| 09-Sep-2004 | 1 | First release |
| 08-Aug-2006 | 2 | New template, SOA updated |

Obsolete Product(s) - Obsolete Product(s)

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